# 4-Bit D-Type Register with Three-State Outputs

The MC14076B 4–Bit Register consists of four D–type flip–flops operating synchronously from a common clock. OR gated output–disable inputs force the outputs into a high–impedance state for use in bus organized systems. OR gated data–disable inputs cause the Q outputs to be fed back to the D inputs of the flip–flops. Thus they are inhibited from changing state while the clocking process remains undisturbed. An asynchronous master root is provided to clear all four flip–flops simultaneously independent of the clock or disable inputs.

#### **Features**

- Three-State Outputs with Gated Control Lines
- Fully Independent Clock Allows Unrestricted Operation for the Two Modes: Parallel Load and Do Nothing
- Asynchronous Master Reset
- Four Bus Buffer Registers
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low-Power TTL Loads or One Low-Power Schottky TTL Load Over the Rated Temperature Range
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant



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SOIC-16 D SUFFIX CASE 751B

#### **MARKING DIAGRAM**



= Assembly Location

 $\begin{array}{ll} \text{WL, L} &= \text{Wafer Lot} \\ \text{YY, Y} &= \text{Year} \\ \text{WW, W} &= \text{Work Week} \\ \text{G} &= \text{Pb-Free Package} \end{array}$ 

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

#### **MAXIMUM RATINGS** (Voltages Referenced to V<sub>SS</sub>)

Symbol	Parameter	Value	Unit
$V_{DD}$	DC Supply Voltage Range	-0.5 to +18.0	V
V <sub>in</sub> , V <sub>out</sub>	Input or Output Voltage Range (DC or Transient)	-0.5 to V <sub>DD</sub> + 0.5	V
I <sub>in</sub> , I <sub>out</sub>	Input or Output Current (DC or Transient) per Pin	±10	mA
$P_{D}$	Power Dissipation, per Package (Note 1)	500	mW
T <sub>A</sub>	Ambient Temperature Range	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

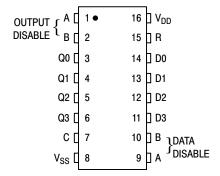
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \le (V_{in} \text{ or } V_{out}) \le V_{DD}$ .

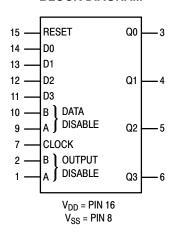
Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V<sub>SS</sub> or V<sub>DD</sub>). Unused outputs must be left open.

<sup>1.</sup> Temperature Derating: "D/DW" Packages: -7.0 mW/°C From 65°C To 125°C

### **PIN ASSIGNMENT**



# **BLOCK DIAGRAM**



## **FUNCTION TABLE**

		Data D	isable	Data	Output
Reset	Clock	Α	В	D	Q
1	Х	Х	Х	Х	0
0	0	Х	Х	X	$Q_n$
0		1	Х	X	$Q_n$
0		Х	1	X	$Q_n$
0		0	0	0	0
0		0	0	1	1

When either output disable A or B (or both) is (are) high the output is disabled to the high-impedance state; however sequential operation of the flip-flops is not affected. X = Don't Care.

#### **ELECTRICAL CHARACTERISTICS** (Voltages Referenced to V<sub>SS</sub>)

				-55	5°C		25°C		125	5°C	
Characteristic		Symbol	V <sub>DD</sub> Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0	"0" Level	V <sub>OL</sub>	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
$V_{in} = 0 \text{ or } V_{DD}$	"1" Level	V <sub>OH</sub>	5.0 10 15	4.95 9.95 14.95	- - -	4.95 9.95 14.95	5.0 10 15	- - -	4.95 9.95 14.95	- - -	Vdc
Input Voltage (V <sub>O</sub> = 4.5 or 0.5 Vdc) (V <sub>O</sub> = 9.0 or 1.0 Vdc) (V <sub>O</sub> = 13.5 or 1.5 Vdc)	"0" Level	V <sub>IL</sub>	5.0 10 15	- - -	1.5 3.0 4.0	- - -	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	V <sub>IH</sub>	5.0 10 15	3.5 7.0 11	- - -	3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11	- - -	Vdc
Output Drive Current $ (V_{OH} = 2.5 \text{ Vdc}) $ $ (V_{OH} = 4.6 \text{ Vdc}) $ $ (V_{OH} = 9.5 \text{ Vdc}) $ $ (V_{OH} = 13.5 \text{ Vdc}) $	Source	ІОН	5.0 5.0 10 15	-3.0 -0.64 -1.6 -4.2	- - -	-2.4 -0.51 -1.3 -3.4	-4.2 -0.88 -2.25 -8.8	- - - -	-1.7 -0.36 -0.9 -2.4	- - -	mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I <sub>OL</sub>	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8	- - -	0.36 0.9 2.4	- - -	mAdc
Input Current		I <sub>in</sub>	15	_	±0.1	-	±0.00001	±0.1	-	±1.0	μAdc
Input Capacitance (V <sub>in</sub> = 0)		C <sub>in</sub>	-	_	-	-	5.0	7.5	_	_	pF
Quiescent Current (Per Package)		I <sub>DD</sub>	5.0 10 15	- - -	5.0 10 20	- - -	0.005 0.010 0.015	5.0 10 20	- - -	150 300 600	μAdc
Total Supply Current (Notes (Dynamic plus Quiescer Per Package) (C <sub>L</sub> = 50 pF on all outpu buffers switching)	nt,	lτ	5.0 10 15			$I_{T} = (1$	.75 μΑ/kHz) .50 μΑ/kHz) .25 μΑ/kHz)	f + I <sub>DD</sub>			μAdc
Three-State Leakage Curre	ent	$I_{TL}$	15	_	±0.1		±0.0001	±0.1		±3.0	μAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics for the listed test conditions, unless otherwise in performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

3. The formulas given are for the typical characteristics only at 25°C.

4. To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where:  $I_T$  is in  $\mu A$  (per package),  $C_L$  in pF,  $V = (V_{DD} - V_{SS})$  in volts, f in kHz is input frequency, and k = 0.002.

# **SWITCHING CHARACTERISTICS** (Note 5) ( $C_L = 50 \text{ pF}, T_A = 25^{\circ}C$ )

Characteristic	Symbol	V <sub>DD</sub> Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise and Fall Time $t_{TLH}, t_{THL} = (1.5 \text{ ns/pF}) C_L + 25 \text{ ns}$ $t_{TLH}, t_{THL} = (0.75 \text{ ns/pF}) C_L + 12.5 \text{ ns}$ $t_{TLH}, t_{THL} = (0.55 \text{ ns/pF}) C_L + 9.5 \text{ ns}$	t <sub>TLH</sub> , t <sub>THL</sub>	5.0 10 15	- - -	100 50 40	200 100 80	ns
Propagation Delay Time  Clock to Q $t_{PLH}$ , $t_{PHL}$ = (1.7 ns/pF) $C_L$ + 215 ns $t_{PLH}$ , $t_{PHL}$ = (0.66 ns/pF) $C_L$ + 92 ns $t_{PLH}$ , $t_{PHL}$ = (0.5 ns/pF) $C_L$ + 65 ns	<sup>t</sup> PLH <sup>, t</sup> PHL	5.0 10 15	- - - -	300 125 90	600 250 180	ns
Reset to Q $t_{PLH}$ , $t_{PHL}$ = (1.7 ns/pF) $C_L$ + 215 ns $t_{PLH}$ , $t_{PHL}$ = (0.66 ns/pF) $C_L$ + 92 ns $t_{PLH}$ , $t_{PHL}$ = (0.5 ns/pF) $C_L$ + 65 ns		5.0 10 15	- - -	300 125 90	600 250 180	
3-State Propagation Delay, Output "1" or "0" to High Impedance	t <sub>PHZ</sub> , t <sub>PLZ</sub>	5.0 10 15	- - -	150 60 45	300 120 90	ns
3-State Propagation Delay, High Impedance to "1" or "0" Level	t <sub>PZH</sub> , t <sub>PZL</sub>	5.0 10 15	- - -	200 80 60	400 160 120	ns
Clock Pulse Width	twн	5.0 10 15	260 110 80	130 55 40	- - -	ns
Reset Pulse Width	t <sub>WH</sub>	5.0 10 15	370 150 110	185 75 55	- - -	ns
Data Setup Time	t <sub>su</sub>	5.0 10 15	30 10 4	15 5 2	- - -	ns
Data Hold Time	t <sub>h</sub>	5.0 10 15	130 60 50	65 30 25	- - -	ns
Data Disable Setup Time	t <sub>su</sub>	5.0 10 15	220 80 50	110 40 25	- - -	ns
Clock Pulse Rise and Fall Time	t <sub>TLH</sub> , t <sub>THL</sub>	5.0 10 15	- - -	- - -	15 5 4	μs
Clock Pulse Frequency	f <sub>cl</sub>	5.0 10 15	- - -	3.6 9.0 12	1.8 4.5 6.0	MHz

<sup>5.</sup> The formulas given are for the typical characteristics only at 25°C.6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

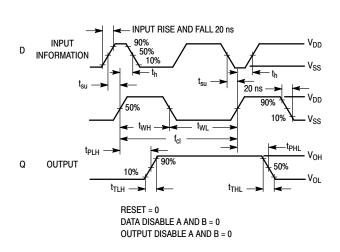


Figure 1. Timing Diagram

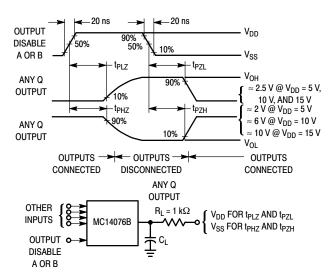
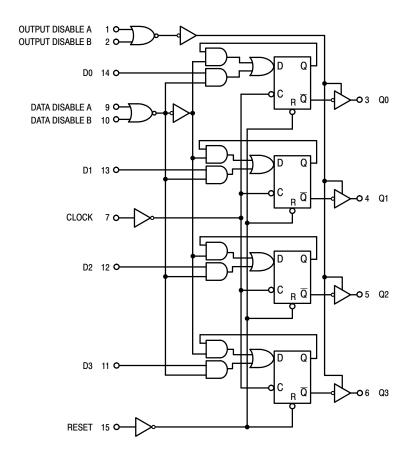


Figure 2. Three-State Propagation Delay Waveshape and Circuit

# EQUIVALENT FUNCTIONAL BLOCK DIAGRAM



### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC14076BDG	SOIC-16 (Pb-Free)	48 Units / Rail
MC14076BDR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
NLV14076BDR2G*	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.



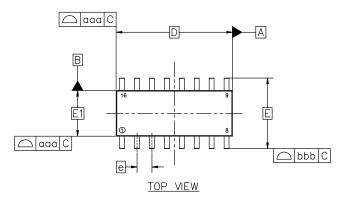


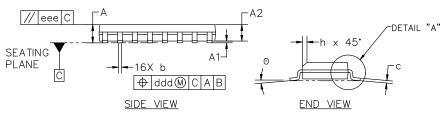
#### SOIC-16 9.90x3.90x1.50 1.27P CASE 751B ISSUE L

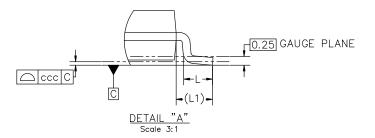
**DATE 29 MAY 2024** 

#### NOTES:

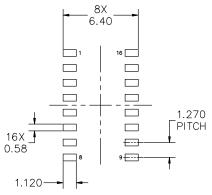
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
- 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
- 5. DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE 6 DIMENSION AT MAXIMUM MATERIAL CONDITION.







MILLIMETERS								
DIM	MIN	NOM	MAX					
А	1.35	1.55	1.75					
A1	0.00	0.05	0.10					
A2	1.35	1.50	1.65					
Ь	0.35	0.42	0.49					
С	0.19	0.22	0.25					
D		9.90 BSC						
E	6.00 BSC							
E1	3.90 BSC							
е	1.27 BSC							
h	0.25		0.50					
L	0.40	0.83	1.25					
L1		1.05 REF						
Θ	0,		7°					
TOLERAN	TOLERANCE OF FORM AND POSITION							
aaa	0.10							
bbb	0.20							
ccc	0.10							
ddd		0.25						
eee	0.10							



#### RECOMMENDED MOUNTING FOOTPRINT

\*FOR ADDITIONAL INFORMATION ON OUR
PB-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE onsemi SOLDERING
AND MOUNTING TECHNIQUES REFERENCE
MANUAL, SOLDERRM/D

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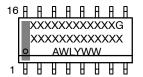
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# SOIC-16 9.90x3.90x1.50 1.27P

CASE 751B ISSUE L

**DATE 29 MAY 2024** 

# GENERIC MARKING DIAGRAM\*



XXXXX = Specific Device Code A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:		STYLE 2:		STYLE 3:	S	TYLE 4:	
	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE #1
	BASE	2.	ANODE	2.	BASE. #1	2.	
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER. #1	3.	
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	
	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	
13.	BASE	13.		13.	COLLECTOR, #4	13.	BASE, #2
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1
STYLE 5:		STYLE 6:		STYLE 7:			
PIN 1.	DRAIN, DYE #1	PIN 1.	CATHODE	PIN 1.	SOURCE N-CH		
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPUT)		
3.	DRAIN. #2	3.	CATHODE	3.	COMMON DRAIN (OUTPUT)		
	שוויאווי, דב	٥.		٥.			
4.		3. 4.	CATHODE	3. 4.			
4. 5.	DRAIN, #2 DRAIN, #3		CATHODE CATHODE		GATE P-CH COMMON DRAIN (OUTPUT)		
5. 6.	DRAIN, #2 DRAIN, #3 DRAIN, #3	4. 5. 6.	CATHODE CATHODE CATHODE	4. 5. 6.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4	4. 5. 6. 7.	CATHODE CATHODE CATHODE CATHODE	4. 5. 6. 7.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5. 6. 7. 8.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4	4. 5. 6. 7.	CATHODE CATHODE CATHODE CATHODE CATHODE	4. 5. 6. 7. 8.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH		
5. 6. 7. 8.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4	4. 5. 6. 7. 8.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	4. 5. 6. 7. 8. 9.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH		
5. 6. 7. 8. 9.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4	4. 5. 6. 7. 8. 9.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE	4. 5. 6. 7. 8. 9.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3	4. 5. 6. 7. 8. 9. 10.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE	4. 5. 6. 7. 8. 9. 10.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10. 11.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3	4. 5. 6. 7. 8. 9. 10. 11.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE	4. 5. 6. 7. 8. 9. 10. 11.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10. 11. 12.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2	4. 5. 6. 7. 8. 9. 10. 11. 12.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE	4. 5. 6. 7. 8. 9. 10. 11. 12.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURGE P-CH SOURGE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH		
5. 6. 7. 8. 9. 10. 11. 12. 13.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 GATE, #4 GATE, #3 SOURCE, #3 GOURCE, #3 GOURCE, #2 SOURCE, #2	4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) CATE N-CH COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2 GATE, #1	4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10. 11. 12. 13.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 GATE, #4 GATE, #3 SOURCE, #3 GOURCE, #3 GOURCE, #2 SOURCE, #2	4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) CATE N-CH COMMON DRAIN (OUTPUT)		

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